

Phonon-assisted optical processes

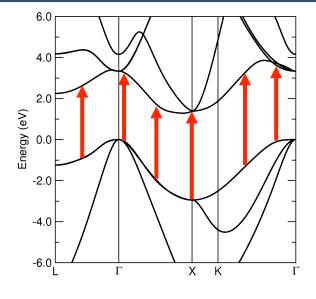
Emmanouil (Manos) Kioupakis

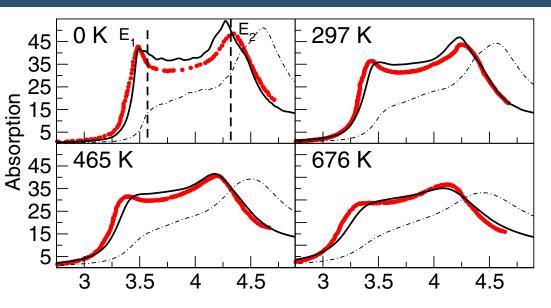
Materials Science and Engineering, University of Michigan kioup@umich.edu

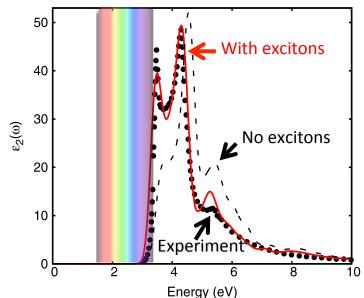
References

- Mark Fox, Optical Properties of Solids, Oxford Master Series in Condensed Matter Physics
- Bassani and Pastori Parravicini, Electronic States and Optical Transitions in Solids, Oxford, New York, Pergamon Press, Chapter 5.
- Feliciano Giustino, Rev. Mod. Phys. 89, 015003 (2017)
- Noffsinger, Kioupakis, Van de Walle, Louie, and Cohen, Phys. Rev. Lett. 108, 167402 (2012)
- Peelaers, Kioupakis, and Van de Walle, *Phys. Rev. B* 92, 235201 (2015)

Motivation: optical absorption in Si







Direct absorption well understood, including excitons and temperature

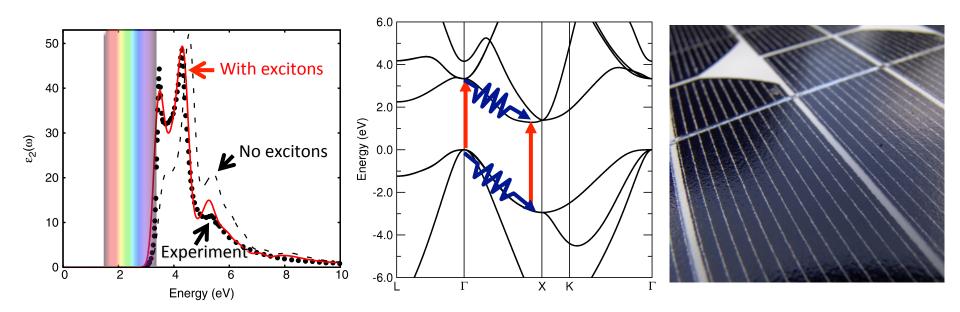
Albrecht, Reining, Del Sole, Onida, *Phys. Rev. Lett.* **80**, 4510 (1998)

Rohlfing and Louie, *Phys. Rev. B* **62**, 4927(2000)

Marini, *Phys. Rev. Lett.* **101**, 106405 (2008)

Deslippe et al., *Comput. Phys. Commun.* **183**, 1269 (2012)

Motivation: silicon solar cells



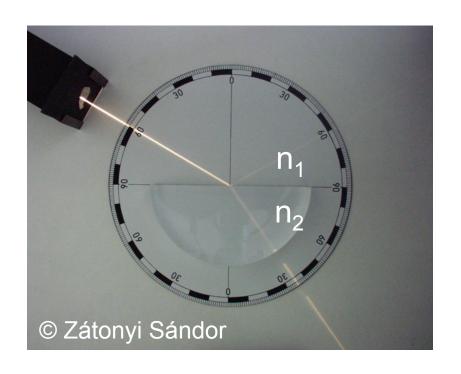
Gap of silicon is indirect (1.2 eV), minimum direct gap is 3.4 eV. Direct optical absorption impossible in the visible. Absorption in the visible is phonon-assisted, enables silicon solar cells.

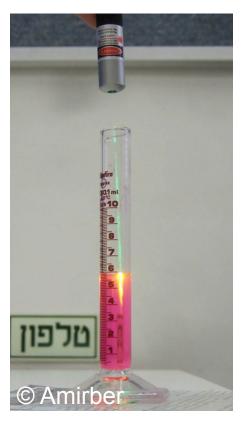
Deslippe et al. Comput. Phys. Commun. **183**, 1269 (2012)

Linear optics

Absorption: Beer-Lambert law

Refraction: Snell's law





$$I(x) = I_0 e^{-\alpha x}$$

 α = absorption coefficient [cm⁻¹] Strong absorbers: $\alpha \sim 10^5 - 10^6$ cm⁻¹

Optical parameters of materials

Complex refractive index:

$$\tilde{n} = n + i\kappa$$

Complex dielectric function:

$$\tilde{\epsilon} = \epsilon_1 + i\epsilon_2$$

Their connection:

$$n = \frac{1}{\sqrt{2}} \left(\epsilon_1 + \left(\epsilon_1^2 + \epsilon_2^2 \right)^{\frac{1}{2}} \right)^{\frac{1}{2}}$$

$$\kappa = \frac{1}{\sqrt{2}} \left(-\epsilon_1 + \left(\epsilon_1^2 + \epsilon_2^2 \right)^{\frac{1}{2}} \right)^{\frac{1}{2}}$$

Absorption coefficient:

$$\alpha = \frac{2\kappa\omega}{c} = \frac{4\pi\kappa}{\lambda}$$

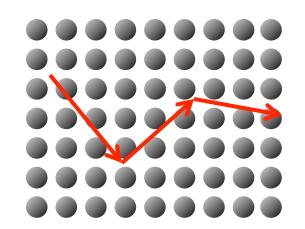
Classical theory of light absorption

Semiclassical Drude model:

$$m^*rac{dec{v}}{dt}=-eec{E}-rac{m^*ec{v}}{ au}$$

e.g., DC conductivity: $\sigma = \frac{ne^2 au}{m^*}$

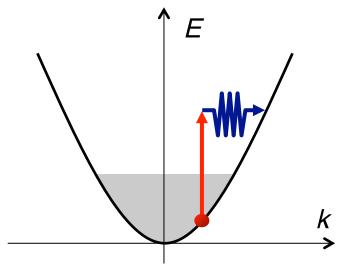
$$\sigma = \frac{ne^2\tau}{m^*}$$



AC field: Absorption coefficient in metals

$$\alpha(\omega) = \frac{4\pi n e^2}{m^* n_r c \tau} \frac{1}{\omega^2}$$

But: **T**: Phenomenological



Quantum theory of optical absorption

Treat with perturbation theory

Unperturbed state = DFT of GW wave functions and eigenvalues

Perturbation: electron-photon Hamiltonian

$$H_{\text{el-phot}} = \frac{e}{mc} \vec{A} \cdot \vec{p}$$

Recombination probability per unit time:

$$P_{i \to f} = \frac{2\pi}{\hbar} \left| \langle f | H_{\text{el-phot}} | i \rangle \right|^2 \delta(E_f - E_i)$$

Initial and final states: $E_i = \varepsilon_{n{m k}}, E_f = \varepsilon_{m{m k}} + \hbar \omega$

Absorbed power: $\hbar\omega\sum_{i,f}(f_i-f_f)P_{i o f}$

Incident power: $\frac{n^2 A^2 \omega^2}{n^2 a^2 \omega^2}$

Quantum theory of optical absorption

Absorption coefficient:

$$\alpha = \frac{\hbar\omega\sum_{i,f}(f_i - f_f)P_{i\to f}}{\frac{n^2A^2\omega^2}{2\pi c^2}}$$
 $p = \text{optical matrix elements}$ $n = 1$ and $n = 1$

Dielectric function:

Imaginary:

$$\epsilon_2 = \frac{n_r c}{\omega} = 2 \frac{4\pi^2 e^2}{m_e^2 \omega^2} \frac{1}{N_k} \sum_{n,m,k} (f_{nk} - f_{mk}) |\boldsymbol{\lambda} \cdot \boldsymbol{p}_{nm}|^2 \delta(\varepsilon_{mk} - \varepsilon_{nk} - \hbar \omega)$$

Real: from Kramers-Kronig relation:

$$\epsilon_1 = 1 + 2 \frac{8\pi e^2}{m_e^2} \frac{1}{N_{\mathbf{k}}} \sum_{n,m,\mathbf{k}} (f_{n\mathbf{k}} - f_{m\mathbf{k}}) \frac{|\boldsymbol{\lambda} \cdot \boldsymbol{p}_{nm}|^2}{(\varepsilon_{m\mathbf{k}} - \varepsilon_{n\mathbf{k}})/\hbar} \frac{1}{(\varepsilon_{m\mathbf{k}} - \varepsilon_{n\mathbf{k}})^2/\hbar^2 - \omega^2}$$

Phonon-assisted optical absorption

Second order perturbation theory

Perturbation: electron-photon + electron-phonon Hamiltonian

$$P_{i \to f} = \frac{2\pi}{\hbar} \left| \sum_{m} \frac{\langle f|H|m\rangle\langle m|H|i\rangle}{E_m - E_i} \right|^2 \delta(E_f - E_i)$$

Keeping cross terms only (other terms are two-photon and two-phonon absorption/emission:

$$P_{i \to f} = \frac{2\pi}{\hbar} \left| \sum_{m} \frac{\langle f | H_{\text{el-phot}} | m \rangle \langle m | H_{\text{el-phon}} | i \rangle}{E_m - E_i} + \sum_{m'} \frac{\langle f | H_{\text{el-phon}} | m' \rangle \langle m' | H_{\text{el-phot}} | i \rangle}{E_{m'} - E_i} \right|^2 \delta(E_f - E_i)$$

Phonon-assisted optical absorption

Absorption coefficient:

$$\alpha = 2\frac{4\pi^2e^2}{n_rcm_e^2\omega}\frac{1}{N_{\boldsymbol{k}}N_{\boldsymbol{q}}}\sum_{i,j,\boldsymbol{k},\boldsymbol{q}}P\left|\boldsymbol{\lambda}\cdot(\boldsymbol{S}_1+\boldsymbol{S}_2)\right|^2\begin{vmatrix}\boldsymbol{p} & \text{optical formula}\\ \boldsymbol{g} = \text{electron-phonon coupling}\\ \boldsymbol{\lambda} = \text{light polarization}\end{vmatrix}$$

p = optical matrix elements

$$m{S}_1(m{k},m{q}) = \! \sum_m rac{m{p}_{im}(m{k}) g_{mj,
u}^{ ext{el-ph}}(m{k},m{q})}{\epsilon_{mm{k}} - \epsilon_{im{k}} - \hbar \omega}$$

$$m{S}_2(m{k},m{q}) = \! \sum_m rac{g_{im,
u}^{ ext{el-ph}}(m{k},m{q})m{p}_{mj}(m{k}+m{q})}{\epsilon_{m,m{k}+m{q}}-\epsilon_{im{k}}\pm\hbar\omega_{
um{q}}}$$

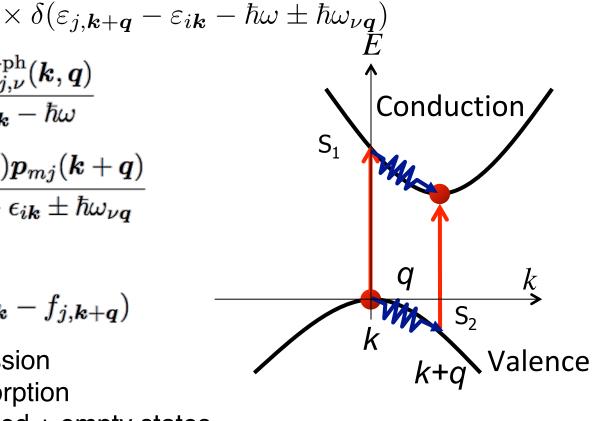
Occupations:

$$P = \left(n_{\nu \boldsymbol{q}} + \frac{1}{2} \pm \frac{1}{2}\right) \left(f_{i\boldsymbol{k}} - f_{j,\boldsymbol{k}+\boldsymbol{q}}\right)$$

Upper sign: phonon emission

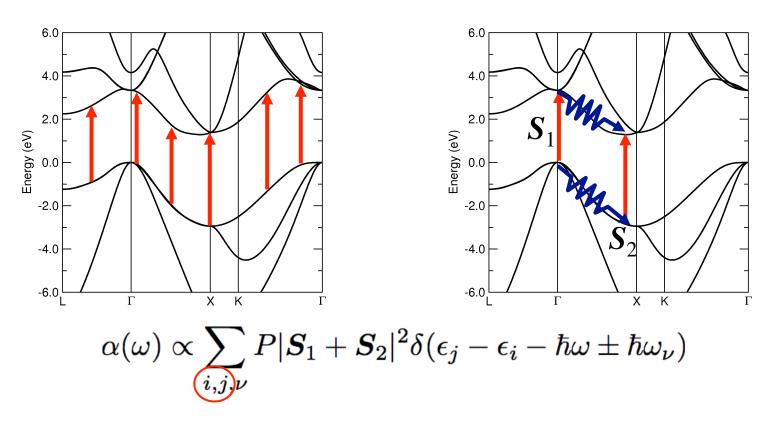
Lower sign: phonon absorption

Sum over *m*: both occupied + empty states



Computational challenge

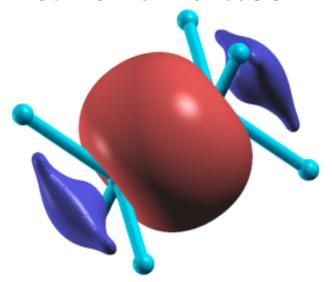
Direct: single sum vs. Indirect: double sum



Double sum over all initial and final states is **expensive**:
For energy resolution of 0.03 eV → need 24×24×24 k-grid and q-grid, ~200M combinations of initial and final wave vectors

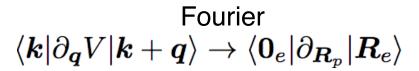
Solution: Wannier interpolation

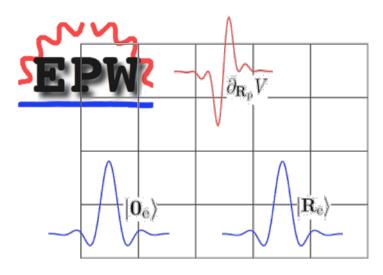
Max. localized Wannier functions From Bloch to Wannier basis



Interpolate *quasiparticle energies*, optical matrix elements.

Mostofi, Yates, Pizzi, Lee, Souza, Vanderbilt, Marzari, *Comput. Phys. Commun.* **185**, 2309 (2014). http://www.wannier.org/





Interpolate *electron-phonon matrix elements.*

Current version: optical matrix elements = momentum operator.

S. Poncé et al, *Comput. Phys. Comm.* **209**, 116 (2016) http://epw.org.uk/

Measuring direct and indirect band gaps

How does experiment determine whether a measured gap in optical absorption is direct or indirect?

A: Tauc plot

For direct absorption: 0 0.75 1.00 1.25 1.50 1.75 2.00 Energy (ev) $\alpha \propto \frac{(\hbar\omega-E_g^d)^{1/2}}{\omega} \Rightarrow (\alpha\omega)^2 \propto \hbar\omega-E_g^d \qquad \text{J. Am. Chem. Soc. 2013, 135, 1213–1216}$

For indirect absorption:

$$\alpha \propto \frac{(\hbar\omega - E_g^i \pm \hbar\omega_{\text{phonon}})^2}{\omega} \Rightarrow$$

$$\Rightarrow (\alpha\omega)^{1/2} \propto \hbar\omega - E_g^i \pm \hbar\omega_{\text{phonon}}$$

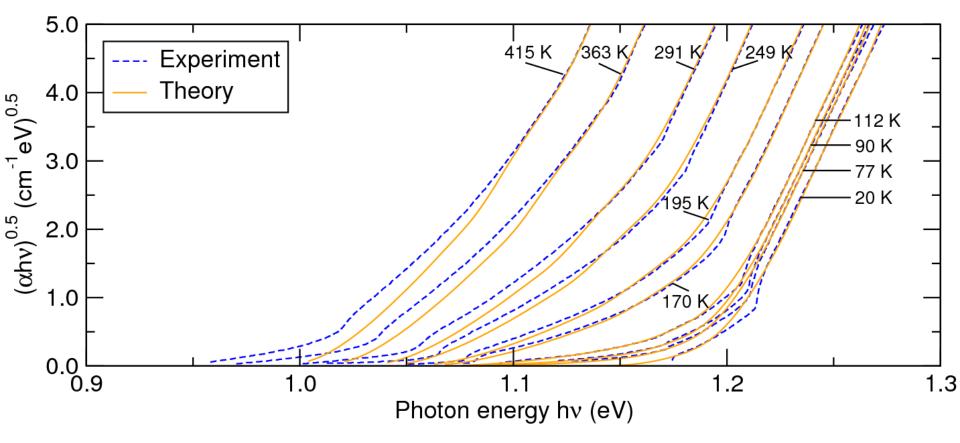
SnSe NSs SnSe NFs

F(R)hv]^{1/2}

Exponent determines type and value of gap.

Two indirect terms for emission/absorption.

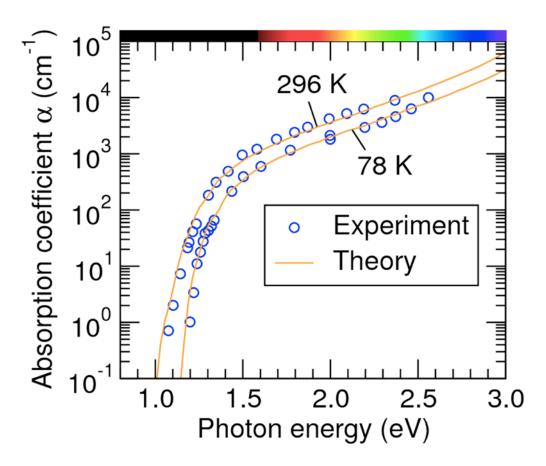
Indirect absorption edge for silicon



Noffsinger, Kioupakis, Van de Walle, Louie, and Cohen, *Phys. Rev. Lett.* **108**, 167402 (2012)

^{*} Shifted the energy of onset by 0.15-0.23 eV to match experimental linear region

Si absorption in the visible



Noffsinger, Kioupakis, Van de Walle, Louie, and Cohen, *Phys. Rev. Lett.* **108**, 167402 (2012)

^{*} Shifted the energy of onset to match experimental trend

Laser diodes

Blu-ray laser diodes (405 nm, violet) based on GaN

Applications:

- Optical storage
- Laser projectors

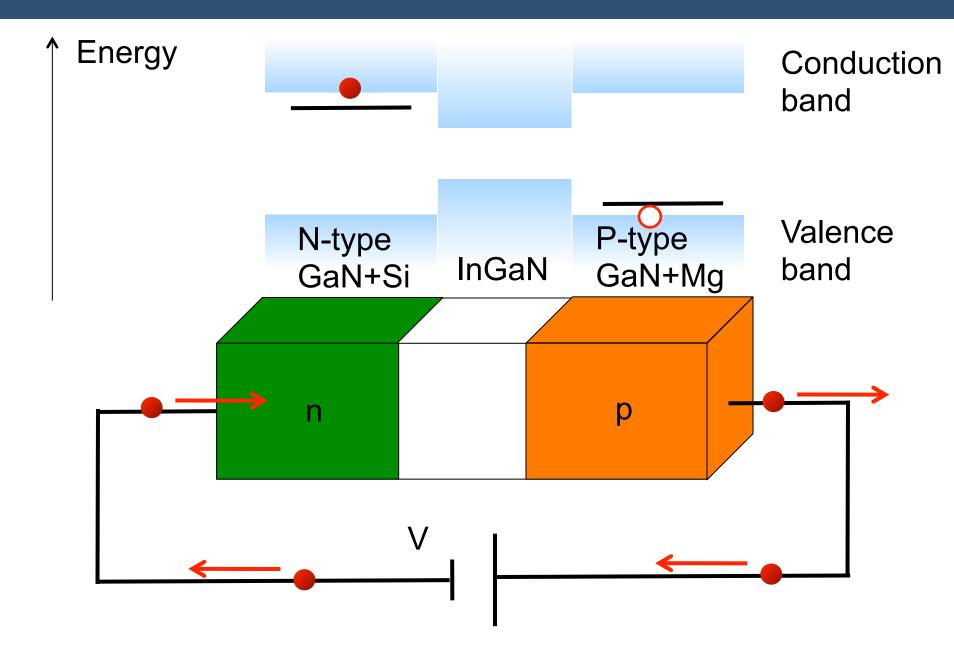




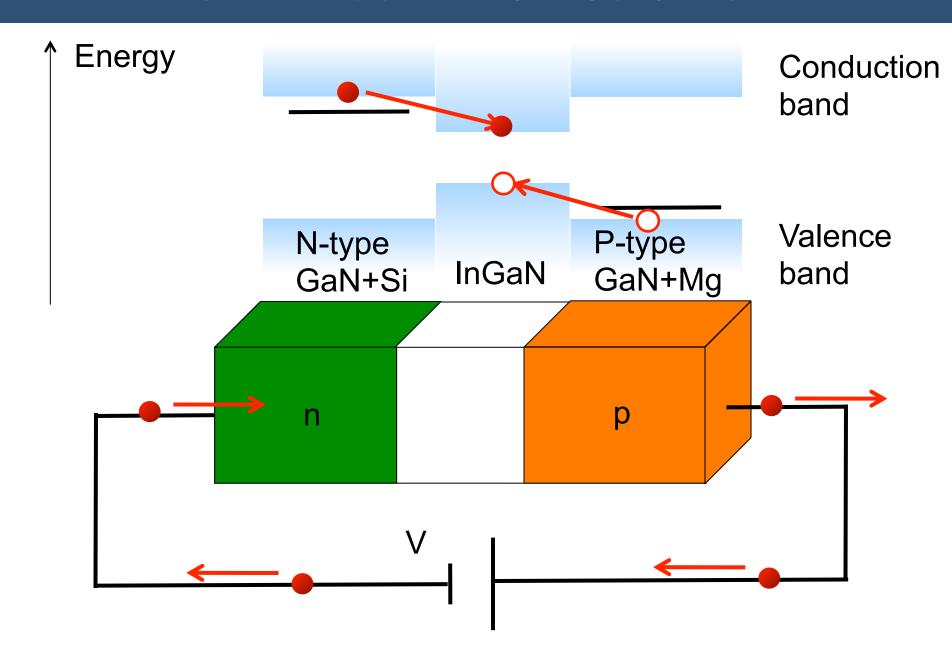
Aim: high-power nitride green lasers.



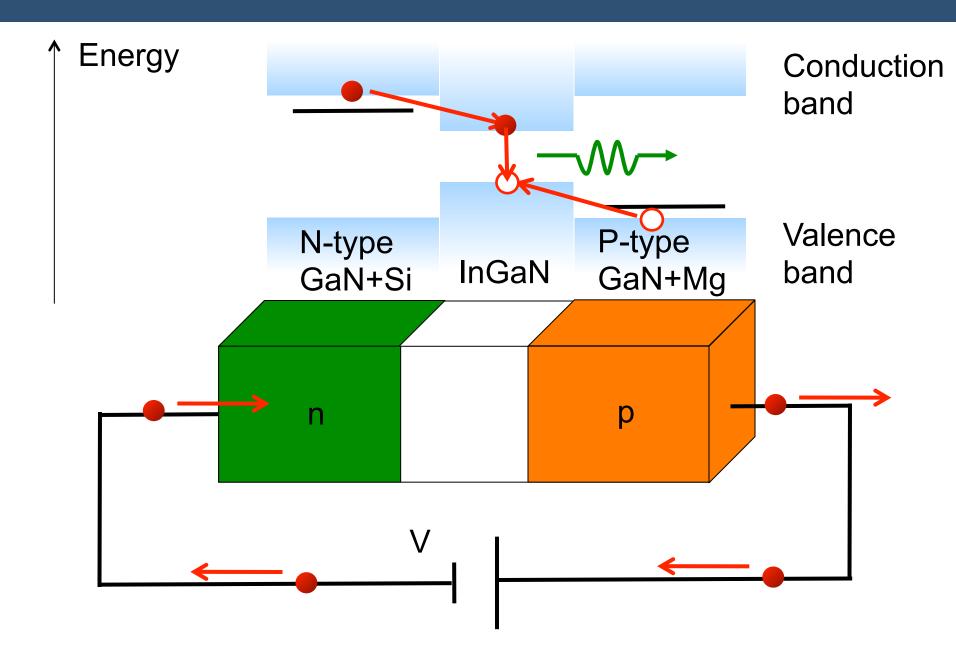
How nitride LEDs/lasers work

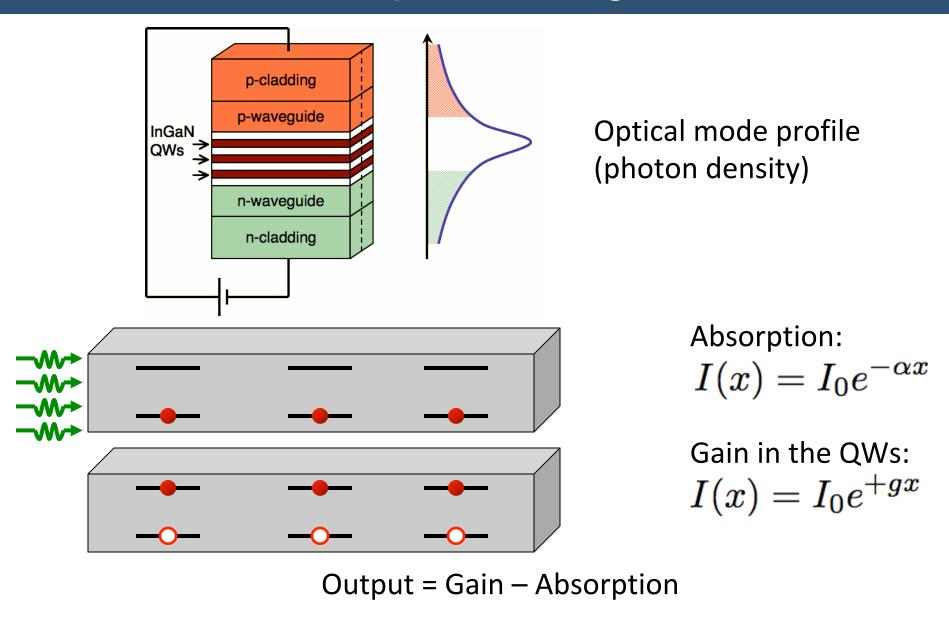


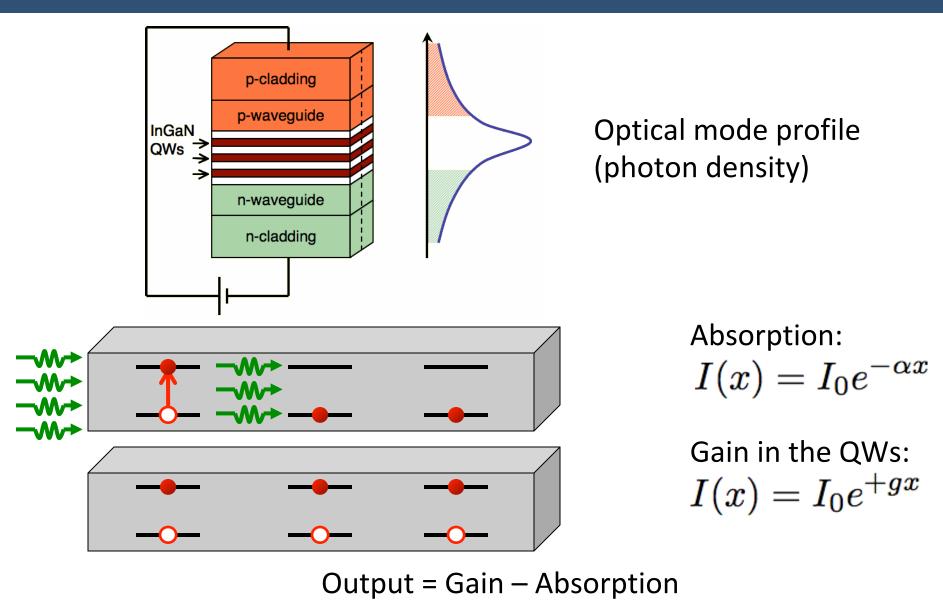
How nitride LEDs/lasers work

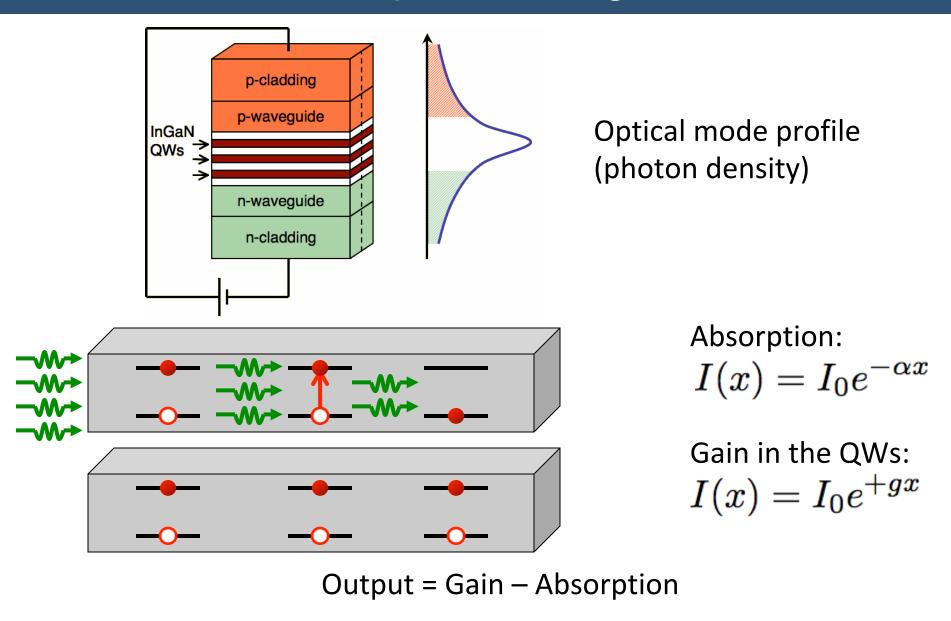


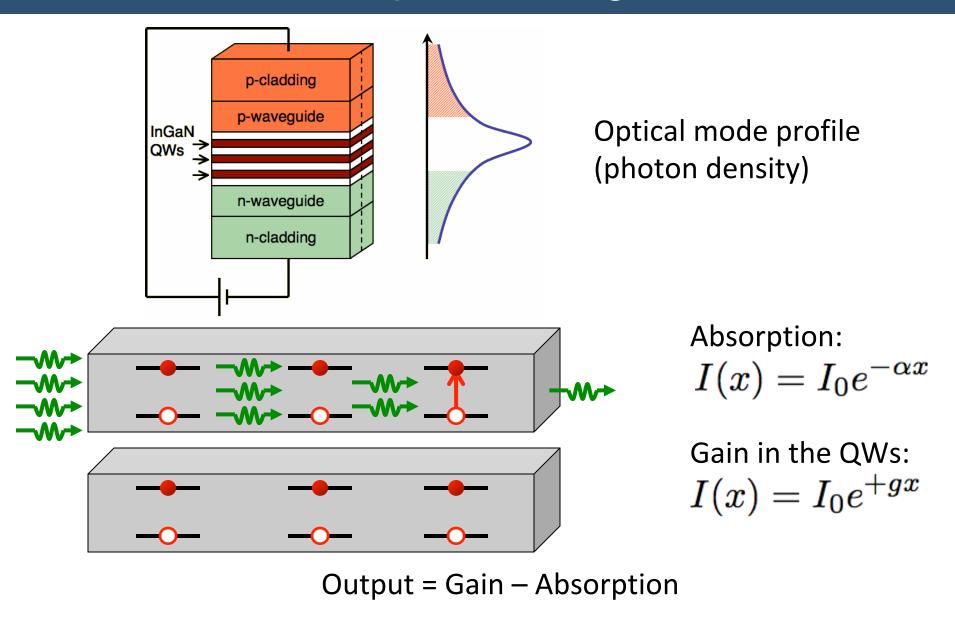
How nitride LEDs/lasers work

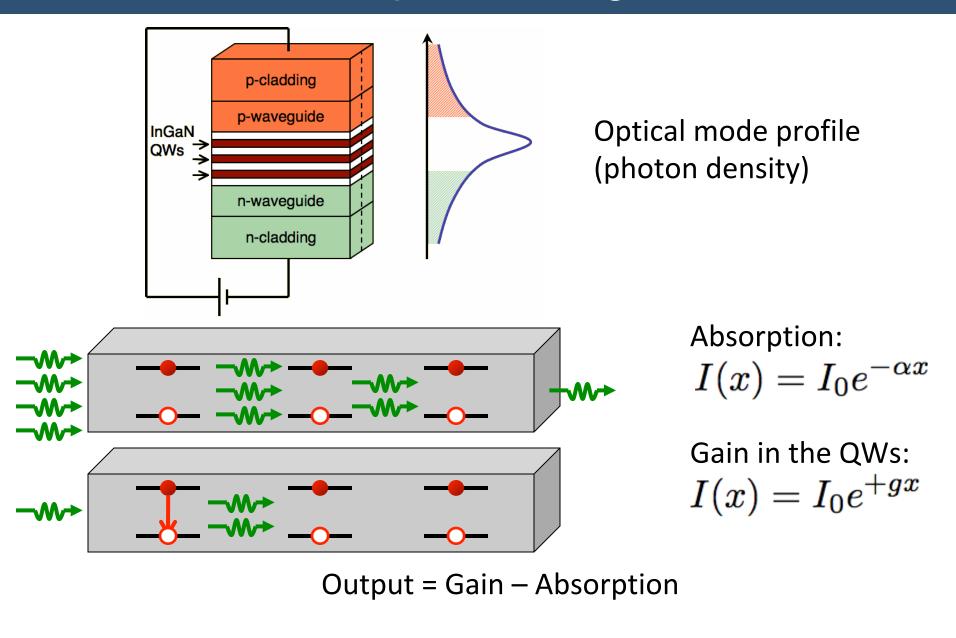


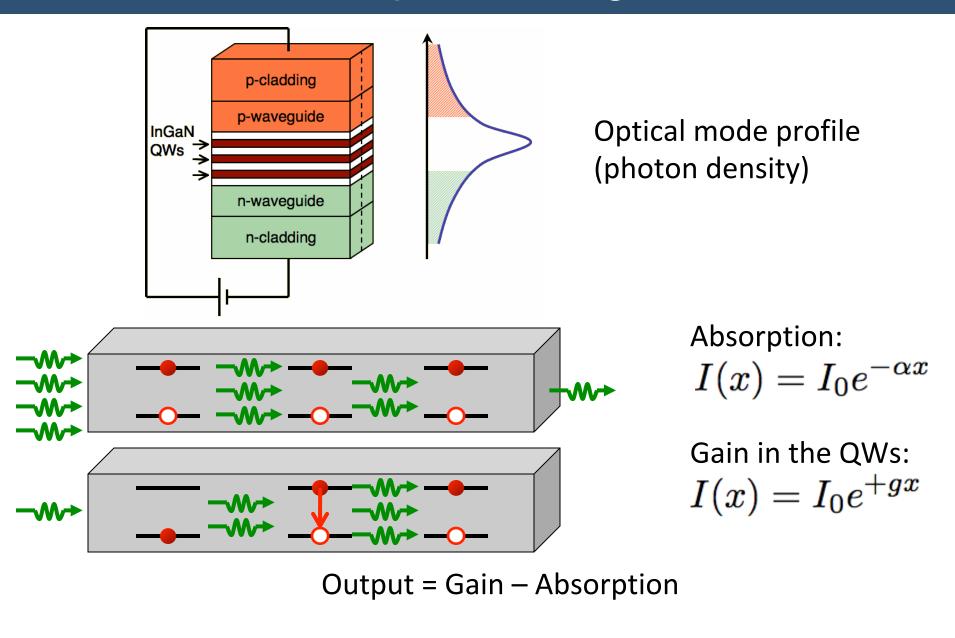


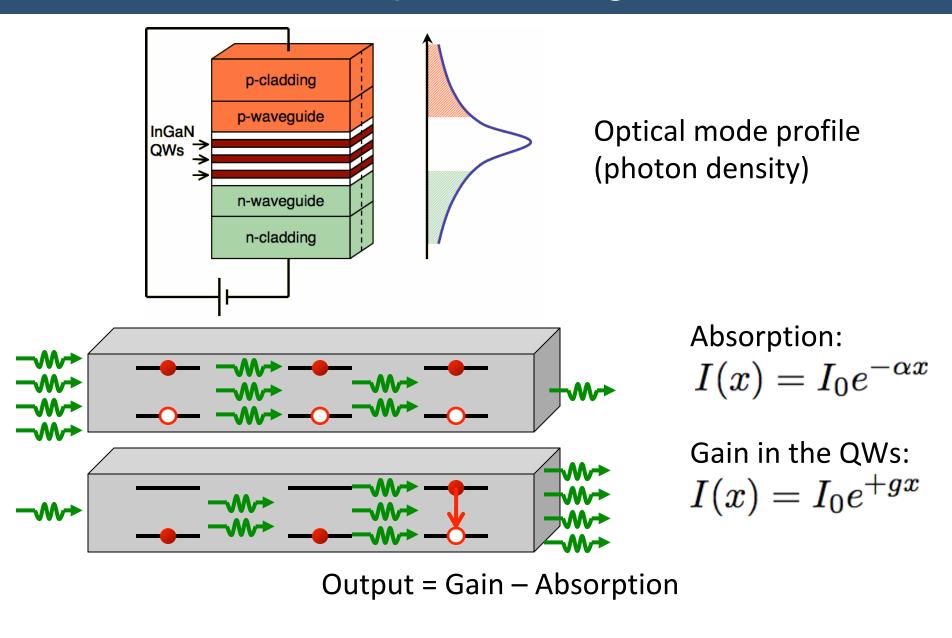






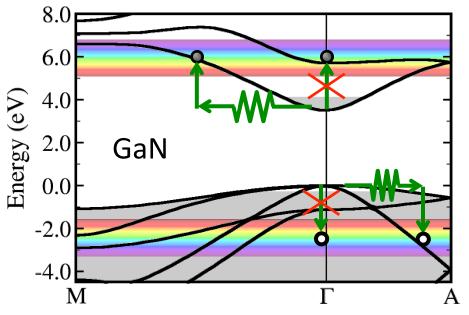






Free-carrier absorption

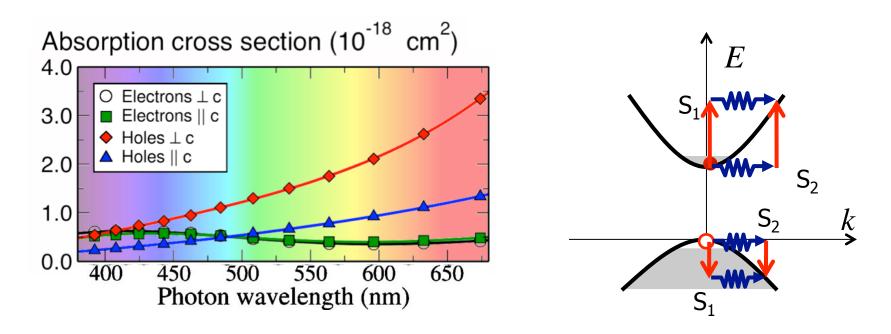
Band gap wider than photon energy, no absorption across gap High concentration of free carriers in lasers, free-carrier absorption a potential source of loss



- Direct absorption is weak:
- Holes: impossible
- Electrons: dipole-forbidden
- Phonon-assisted absorption:

Possible for every photon energy

Phonon-assisted free-carrier absorption

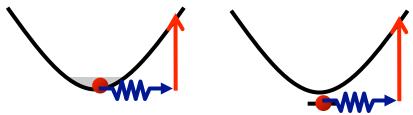


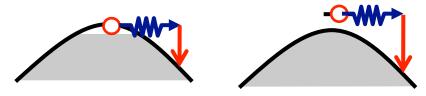
Absorption cross section σ : $\alpha = n\sigma$

For $n=10^{19}$ cm⁻³ (lasers under operating conditions): $\alpha=10$ cm⁻¹ Contrast with direct gap materials: $\alpha=10^5-10^6$ cm⁻¹

Absorption by non-ionized Mg in p-GaN

Absorption by carriers bound to dopants



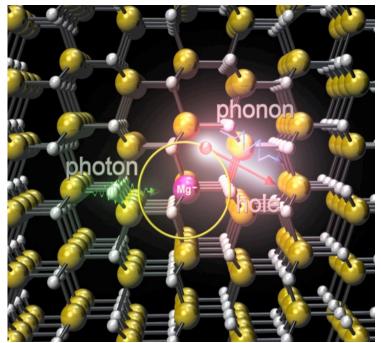


Free carriers *vs.* donor/acceptor bound Activation energies:

GaN:Si: 50 meV

GaN:Mg: 200 meV

Large concentration (10¹⁹ cm⁻³) of non-ionized Mg in p-GaN, causes internal absorption loss, more important at longer wavelengths



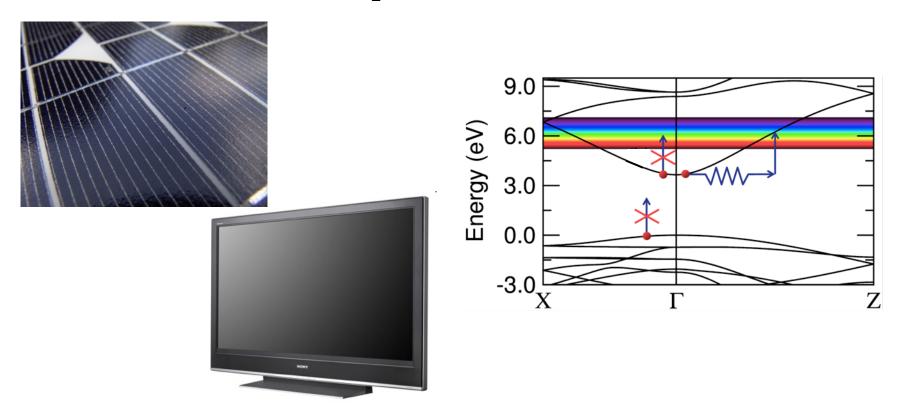
1.) Kioupakis, Rinke, Schleife, Bechstedt, & Van de Walle,

Phys. Rev. B 81, 241201 (2010)

2.) Kioupakis, Rinke, & Van de Walle, Appl. Phys. Express 3, 082101 (2010)

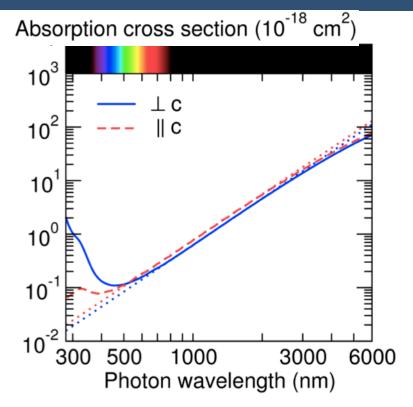
Absorption in transparent conducting oxides

Conducting oxides (e.g. SnO₂) used for transparent electrical contacts



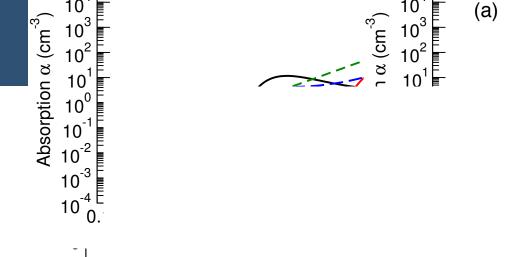
Fundamental transparency limit due to free-carrier absorption

Free-carrier absorption in n-SnO₂



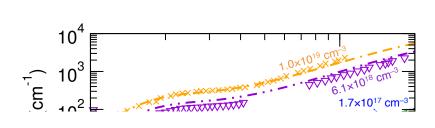
Fundamental limits on optical transparency of transparent conducting oxides: free-carrier absorption in SnO₂

- H. Peelaers, E. Kioupakis, and C. G. Van de Walle
- Appl. Phys. Lett. 100, 011914 (2012)
- Phys. Rev. B 92, 235201 (2015)

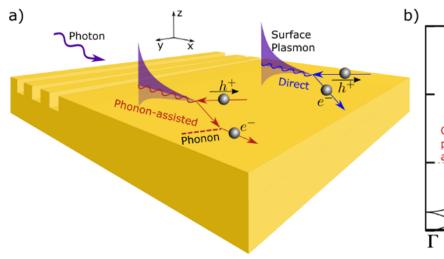


- Absorption of light in n-type silicon competes with interband absorption.
- Also: absorption in the infrared.
- Direct + indirect absorption possible.
- Resignts for α vs. doping in good agregment with experiment.





Plasmon decay in metals



Imaginary part of dielectric function also describes plasmon energy loss in metals

Strong contribution from phononassisted terms

Brown et al., *ACS Nano* **10**, 957–966 (2016)

$$\Gamma = \frac{\omega}{2L(\omega)|\gamma(z<0)|} \lambda^* \cdot \operatorname{Im} \overline{\varepsilon}(\omega) \cdot \lambda$$

$$\lambda^* \cdot \operatorname{Im} \overline{\varepsilon}_{\text{phonon}}(\omega) \cdot \lambda = \frac{4\pi^2 e^2}{m_e^2 \omega^2} \int_{BZ} \frac{\mathrm{d}\mathbf{q}' \mathrm{d}\mathbf{q}}{(2\pi)^6}$$

$$\sum_{n'n\alpha\pm} (f_{\mathbf{q}n} - f_{\mathbf{q}'n'}) \left(n_{\mathbf{q}'-\mathbf{q},\alpha} + \frac{1}{2} \mp \frac{1}{2} \right)$$

$$\delta(\varepsilon_{\mathbf{q}'n'} - \varepsilon_{\mathbf{q}n} - \hbar\omega \mp \hbar\omega_{\mathbf{q}'-\mathbf{q},\alpha}) \times$$

$$\left| \lambda \cdot \sum_{n_1} \left(\frac{g_{\mathbf{q}'n',\mathbf{q}n_1}^{\mathbf{q}'-\mathbf{q},\alpha} \langle \mathbf{p} \rangle_{n_1n}^{\mathbf{q}}}{\varepsilon_{\mathbf{q}n_1} - \varepsilon_{\mathbf{q}n} - \hbar\omega + i\eta} \right) \right|^2$$

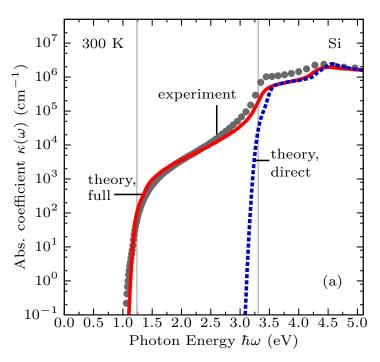
$$+ \frac{\langle \mathbf{p} \rangle_{n'n_1}^{\mathbf{q}'} g_{\mathbf{q}'n_1,\mathbf{q}n}^{\mathbf{q}'-\mathbf{q},\alpha}}{\varepsilon_{\mathbf{q}'n_1} - \varepsilon_{\mathbf{q}n} \mp \hbar\omega_{\mathbf{q}'-\mathbf{q},\alpha} + i\eta} \right) \right|^2$$

Alternative method: Zacharias and Giustino

Calculate direct optical absorption in a single optimal supercell with atoms displaced according to a linear combination of the phonon modes

Advantages:

- Avoids divergence
- No need for Wannier interpolation
- T-dependence of eigenvalues, band gap, and Urbach tail.
- Can be generalized for other functionals, excitons, ...



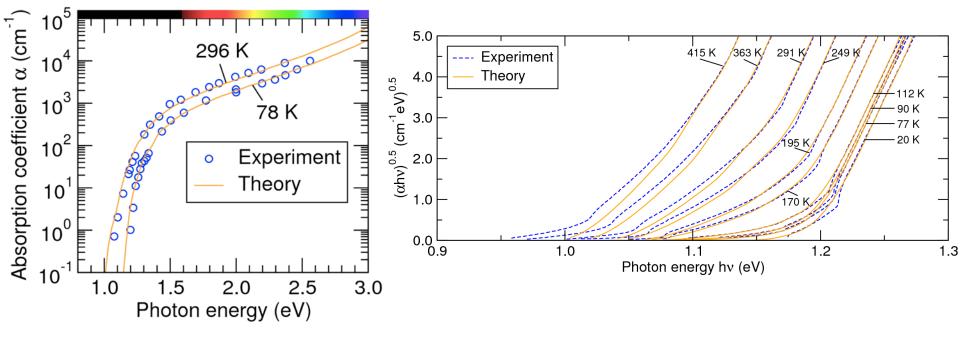
Zacharias and Giustino Physical Review B 94, 075125 (2016)

$$\Delta \tau_{\kappa \alpha} = (M_{\rm p}/M_{\kappa})^{\frac{1}{2}} \sum_{\nu} (-1)^{\nu-1} e_{\kappa \alpha, \nu} \, \sigma_{\nu, T}.$$

$$\sigma_{\nu, T}^{2} = (2n_{\nu, T} + 1) \, l_{\nu}^{2},$$

$$n_{\nu, T} = [\exp(\hbar \omega_{\nu}/k_{\rm B}T) - 1]^{-1}$$

 $l_{\nu} = (\hbar/2M_{\rm p}\Omega_{\nu})^{1/2}$



Acknowledgements

Chris Van de Walle, Hartwin Peelaers (UCSB), Patrick Rinke (Aalto) Steven Louie, Marvin Cohen, Jesse Noffsinger (Berkeley) Andre Schleife (Illinois) and Friedhelm Bechstedt (Jena) Feliciano Giustino, Samuel Poncé, Carla Verdi (Oxford) Roxana Margine (Binghamton), Guangsha Shi (Google)

Thank you for your attention



